



PVD Resists: Environmentally friendly resists using physical vapor deposition

Marie Krysak¹, Frauke Pfeiffer², Christian Neuber², Tristan Kolb²,
Hans-Werner Schmidt² and Christopher K. Ober¹

¹Department of Materials Science and Engineering, Cornell University, Ithaca, NY

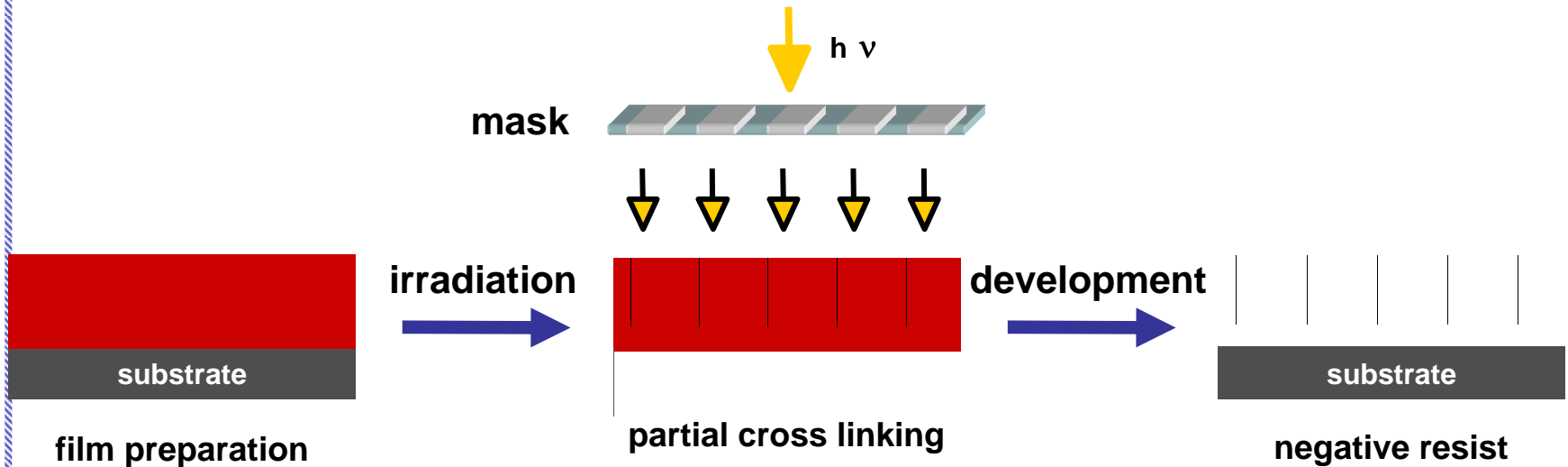
²Makromolekulare Chemie I and Bayreuther Institut für Makromolekülforschung,
Universität Bayreuth, Germany



Outline

- **Physical Vapor Deposition (PVD)**
 - **Process**
 - **Benefits**
 - **Materials Requirements**
- **Novelty of PVD Process**
 - **Combinatorial Processing**
 - **Composition Gradients**
- **All-Dry Lithography**
 - **Processes**
 - **Results**

Solvent Free Photopatterning



Film preparation

solution

state of the art

dry

on going research

Development

solution

state of the art

solution

state of the art



Why Prepare a film via PVD?

Solution-based processes:

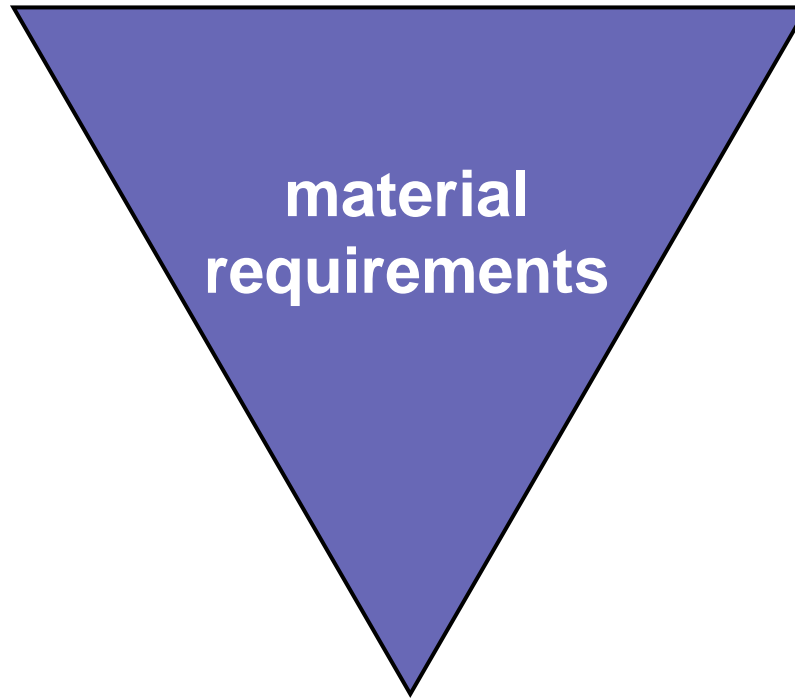
- **solvents has to be dust-free, no impurities**
 - ⇒ defects, pinholes
 - ⇒ rougher surface
 - ⇒ wetting, dewetting phenomena
- **wasteful in terms of solvent use**
- **loss of valuable resist materials**

Physical Vapor Deposition:

- **precise layer thickness control in the nanometer range**
- **resulting films are very uniform**
- **usability of insoluble materials**
- **applicability of a combinatorial PVD approach^{*)}**

Physical Vapor Deposition

**thermally
stability**



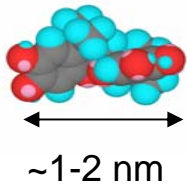
**optimal
molecular weight**

**amorphous
films**

Molecular Glasses

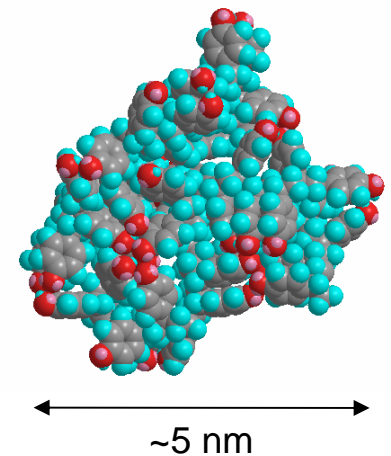
Low molecular weight amorphous materials

- Defined by their bulky, rigid structure
- Thermally stable, high glass transition temperature (T_g)
- Monodisperse
- High purity (purified by common chromatographic techniques)



...As opposed to traditional polymeric resists

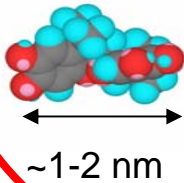
- MW varies from 5,000 to 25,000 g/mol
- polydisperse



Molecular Glasses

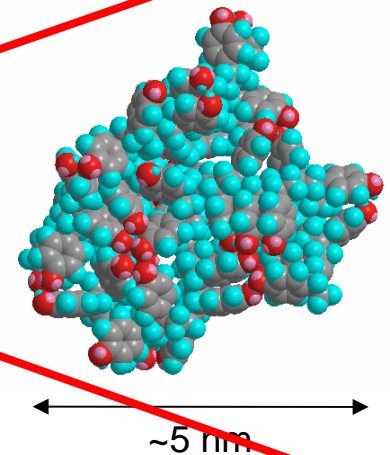
Low molecular weight amorphous materials

- Defined by their bulky, rigid structure
- Thermally stable, high glass transition temperature (T_g)
- Monodisperse
- High purity (purified by common chromatographic techniques)



~~...As opposed to traditional polymeric resists~~

- ~~• MW varies from 5,000 to 25,000 g/mol~~
- ~~• polydisperse~~

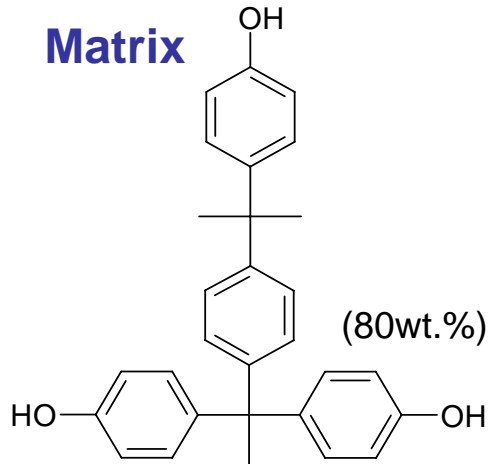


Molecular Glass Photoresists

Advantages:

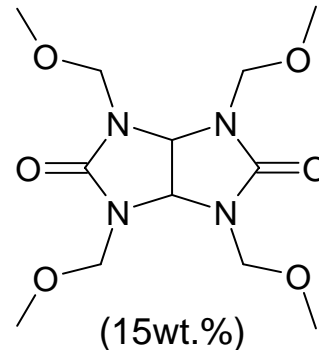
- exact defined molecular weight
- small intrinsic molecular size

Matrix



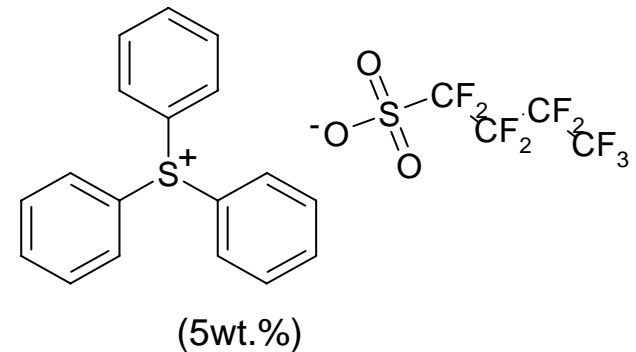
Tris(4-hydroxyphenyl)-
1-ethyl-4-isopropylbenzene

Cross linker



Powderlink® 1174

Photo acid generators



✓ solvent casting

vapor depositable ?

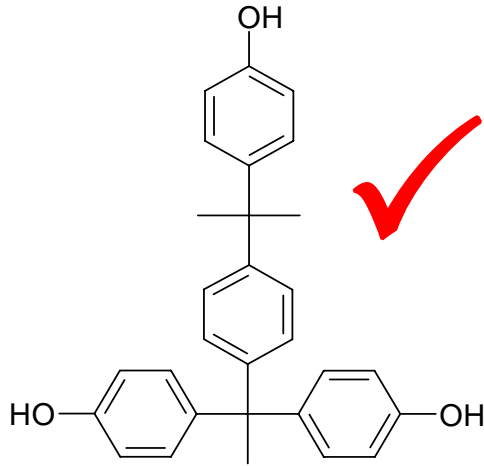
a) D. Yang; S. W. Chang, C. K. Ober, *J. Mater. Chem.* **16**, 1693 (2006); b) J. Dai; S. W. Chang; A. Hamad; D. Yang; N. Felix, C. K. Ober, *Chem. Mater.* **18**, 3404 (2006); c) S. W. Chang; R. Ayothi; D. Bratton; D. Yang; N. Felix; H. B. Cao; H. Deng, C. K. Ober, *J. Mater. Chem.* **16**, 1470 (2006); d) R. Ayothi; S. W. Chang; N. Felix; H. B. Cao; H. Deng; Y. Wang, C. K. Ober, *J. Photopolym. Sci. Technol.* **19**, 515 (2006).

Molecular Glass Photoresists

Vapor deposition materials demand :

thermally stable, sufficient high molecular weight, but not too high,
no crystallization in thin layers, ...

Matrix



Cross linker

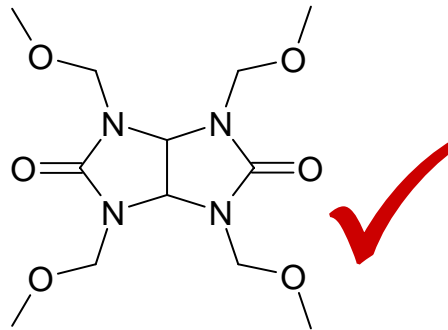
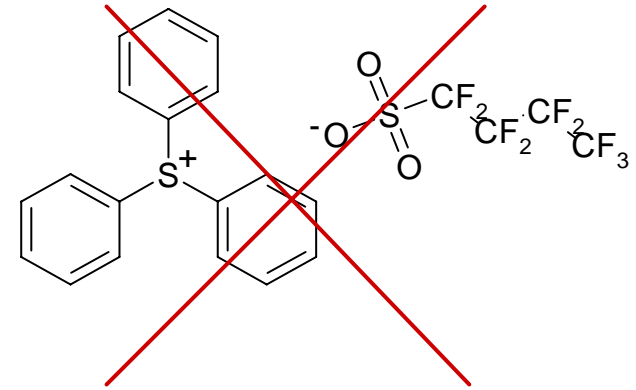


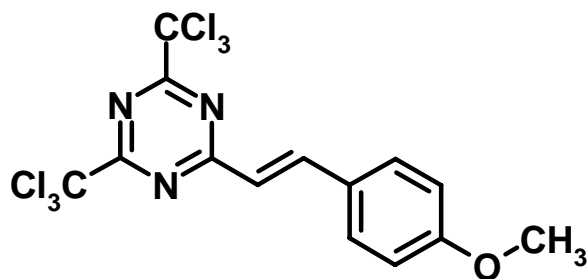
Photo acid generators



Suitable non-ionic PAGs needed

Vapor Depositible Photoacid Generators

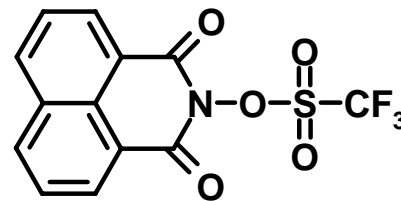
Triazine derivative



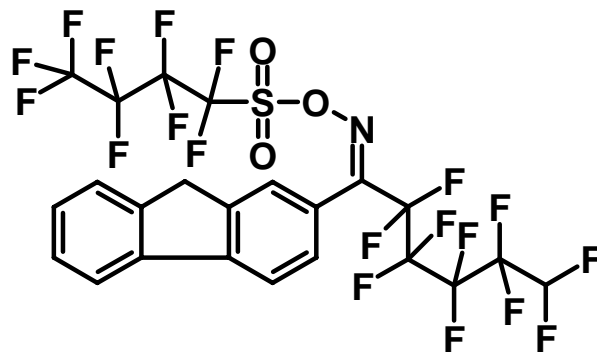
vapor deposition



Triflate



vapor deposition

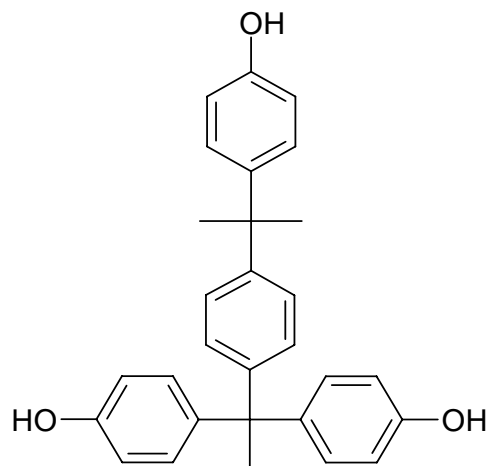


vapor deposition



Vapor Depositible Molecular Glass Photoresists

Matrix



Cross linker

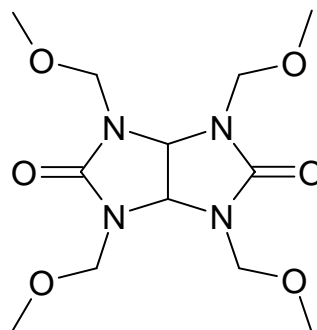
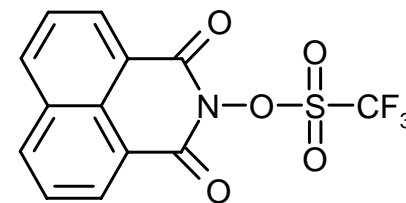
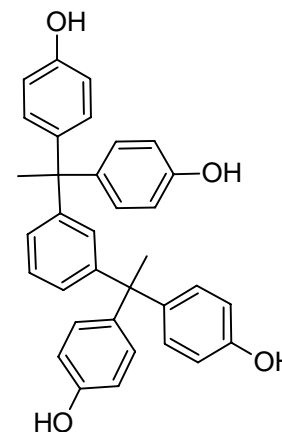
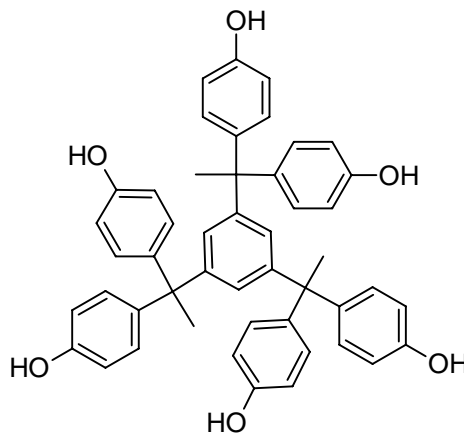
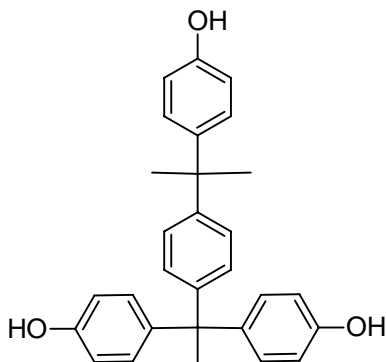
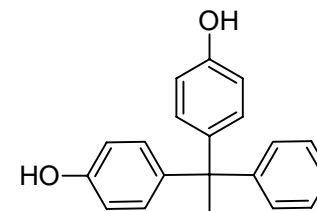
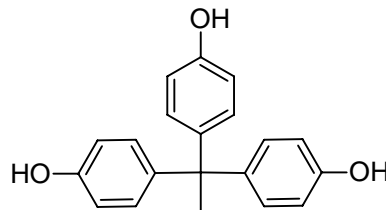
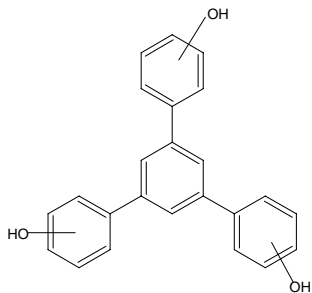


Photo acid generators



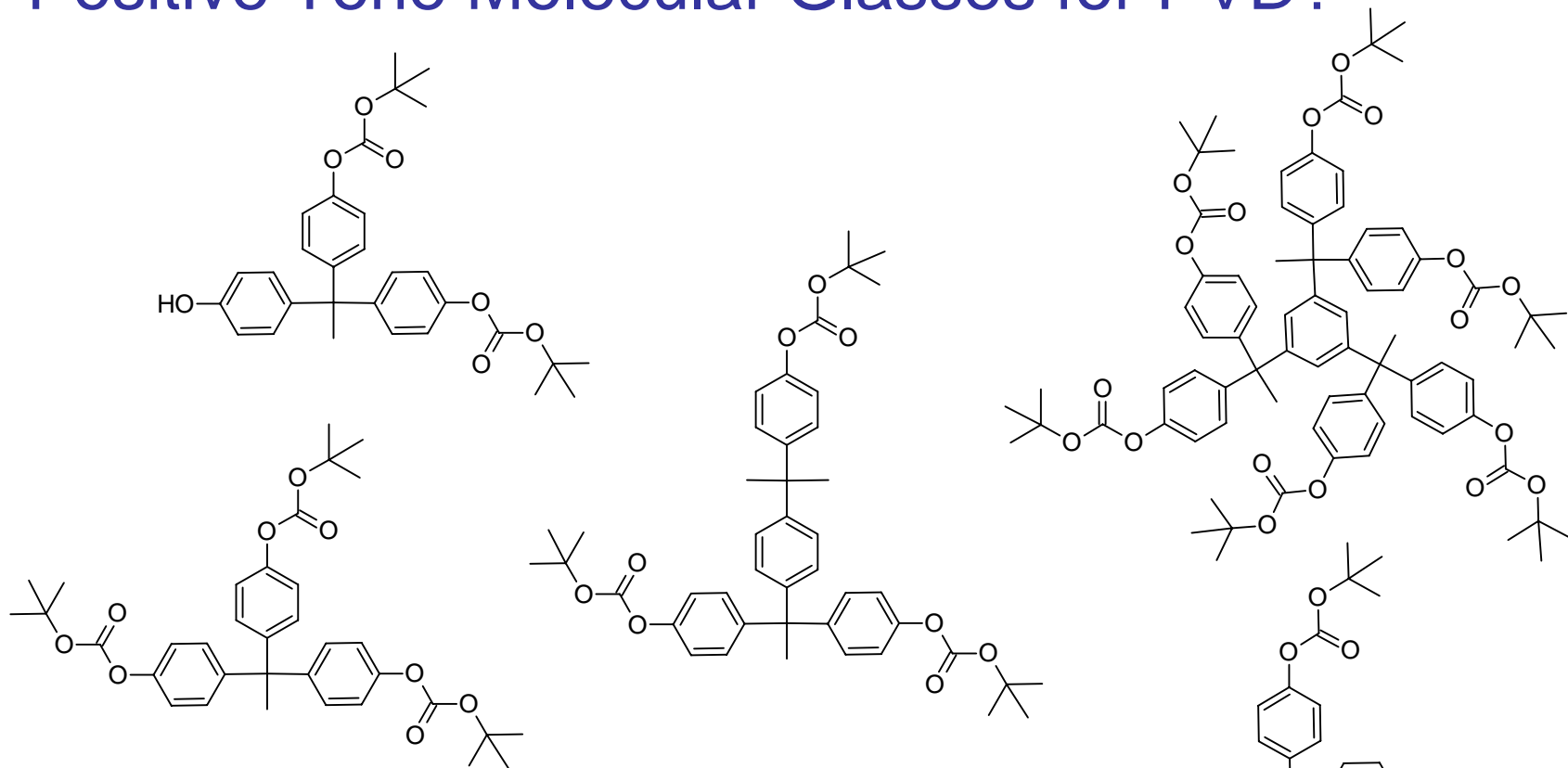
Vapor Deposited Molecular Glasses



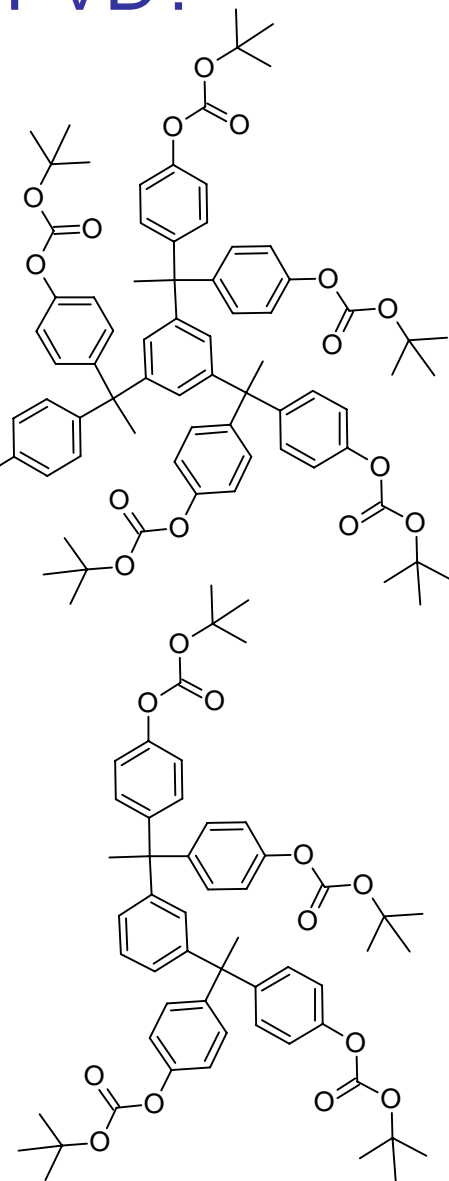
Short list of a complete library of resists

All molecules were used as negative tone resists with vapor deposited crosslinker and non-ionic PAG

Positive Tone Molecular Glasses for PVD?

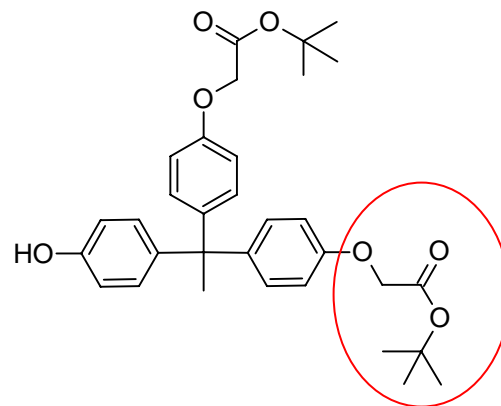
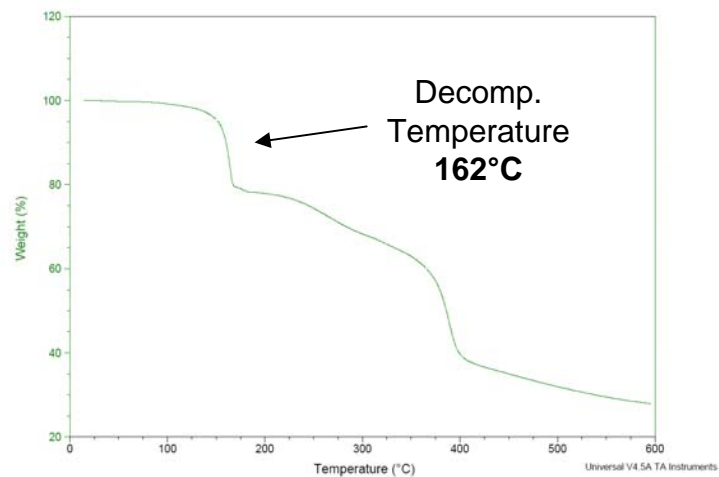
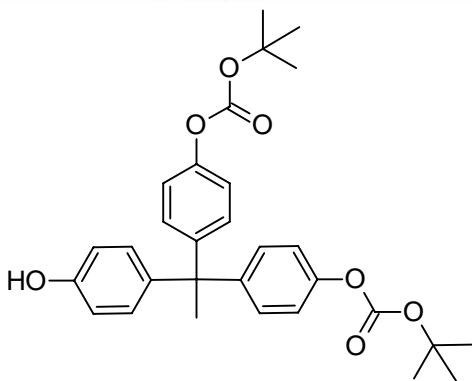
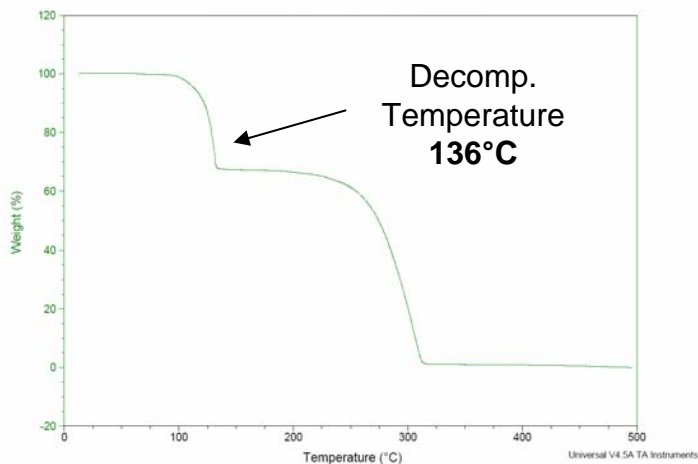


All t-BOC protected molecules showed decomposition during PVD



PVD Protecting Group

TGA curves



Ester protecting group provides better thermal stability

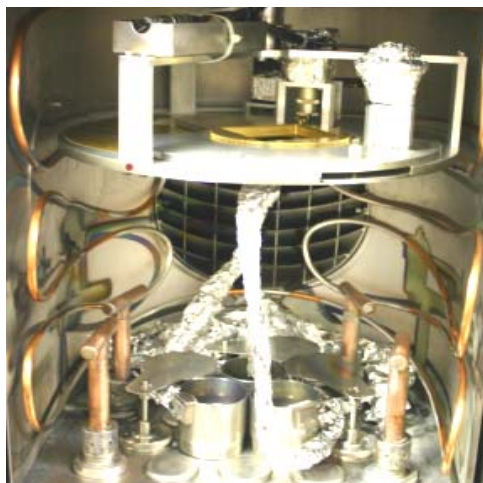


Outline

- Physical Vapor Deposition (PVD)
 - Process
 - Benefits
 - Materials Requirements
- **Novelty of PVD Process**
 - **Combinatorial Processing**
 - Composition Gradients
- All-Dry Lithography
 - Processes
 - Results

Materials Screening and Combinatorial Development of Thin Film Multilayer Electro-Optical Devices

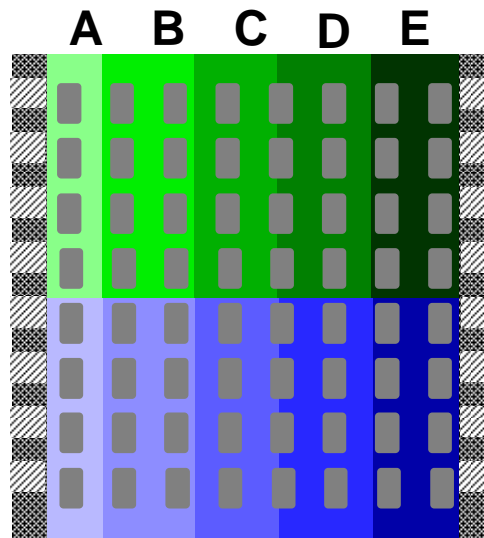
Equipment



Thelakkat, et al.
Macromol. Rapid Commun.
25, 204 (2004).

Neuber, et al.
Rev. Sci. Instrum.
78, 072216/1 (2007).

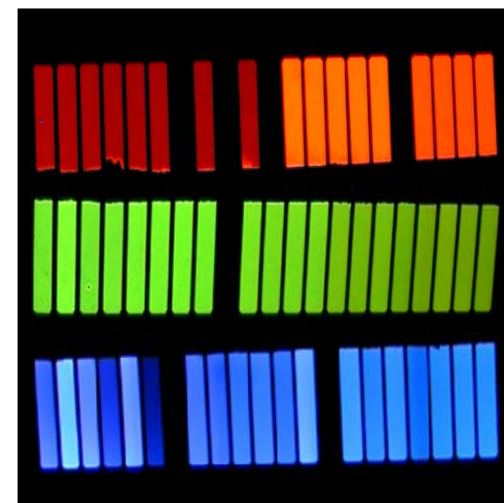
Combinatorial Library



76 x 76 mm

Neuber, et al.
Journal of Materials Chemistry **16**,
3466 (2006).

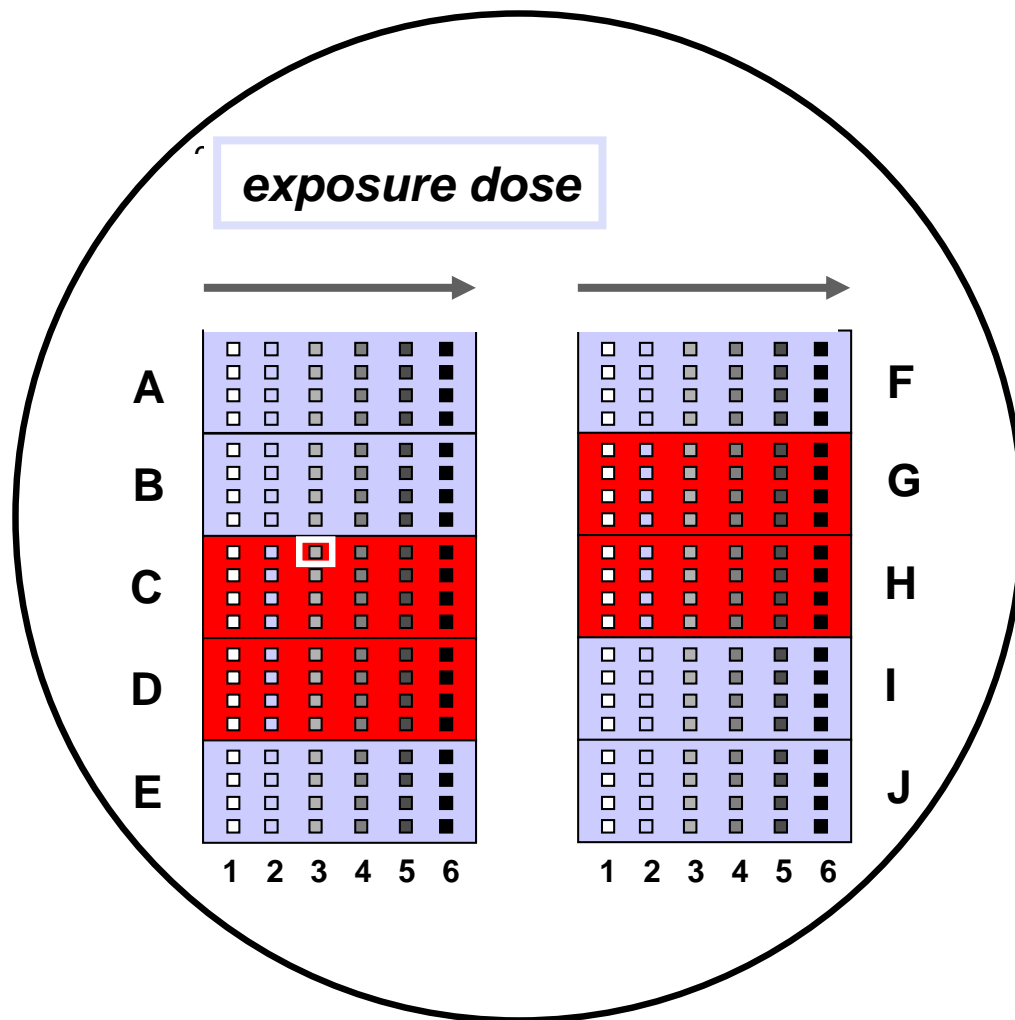
Organic Light Emitting Devices



76 x 76 mm

Kreger et al.
Advanced Functional Materials,
17, 3456 (2007).

Combinatorial Vapor Deposition of Molecular Glass Photoresists



Instrumentation

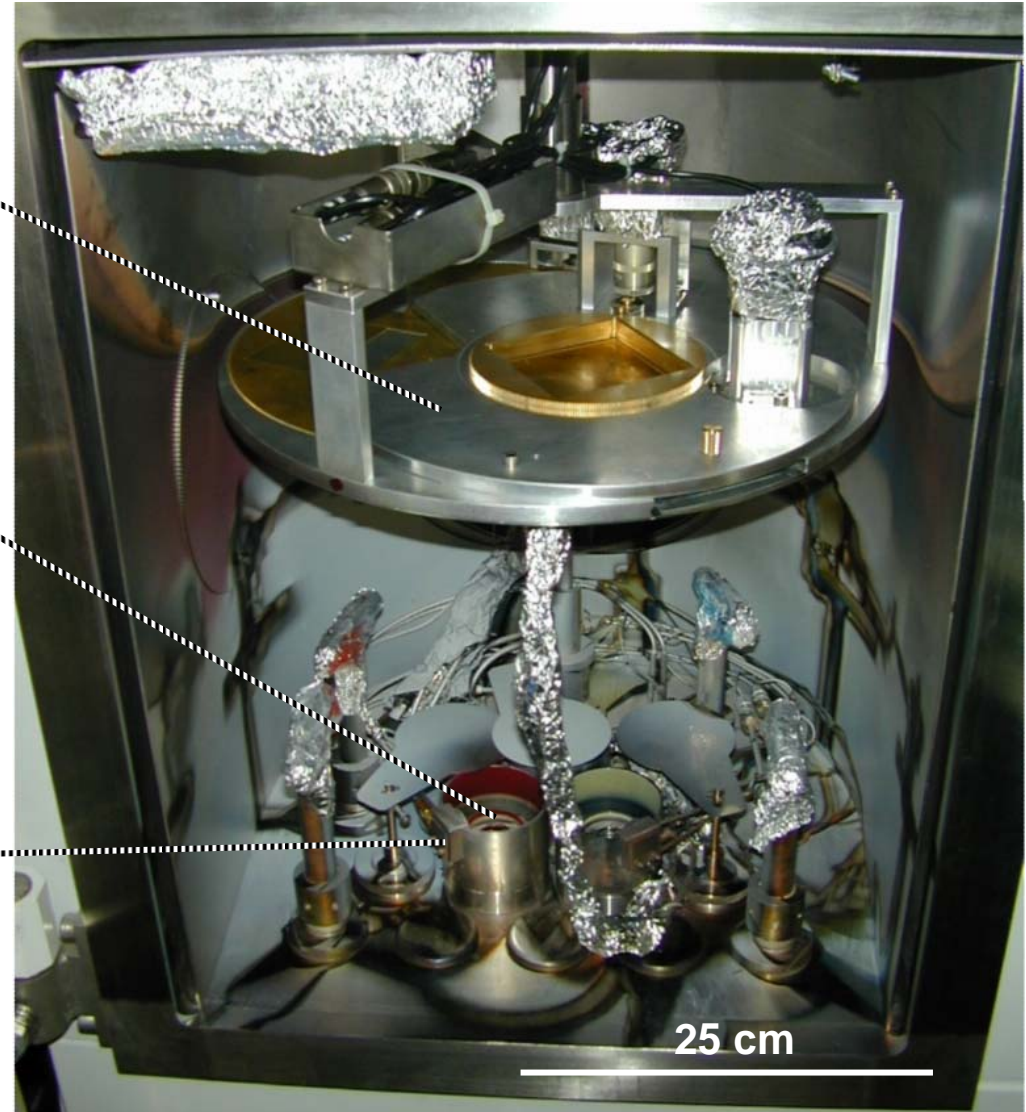
Rotating combinatorial set-up

Sources

- 3 effusion cells (organics)
- 2 sources, controlled by electrical resistance (metals)

Monitoring

- Evaporation rates of each effusion cell controlled by a quartz crystal
- each effusion cell closed by a shutter



Instrumentation

quartz
crystal

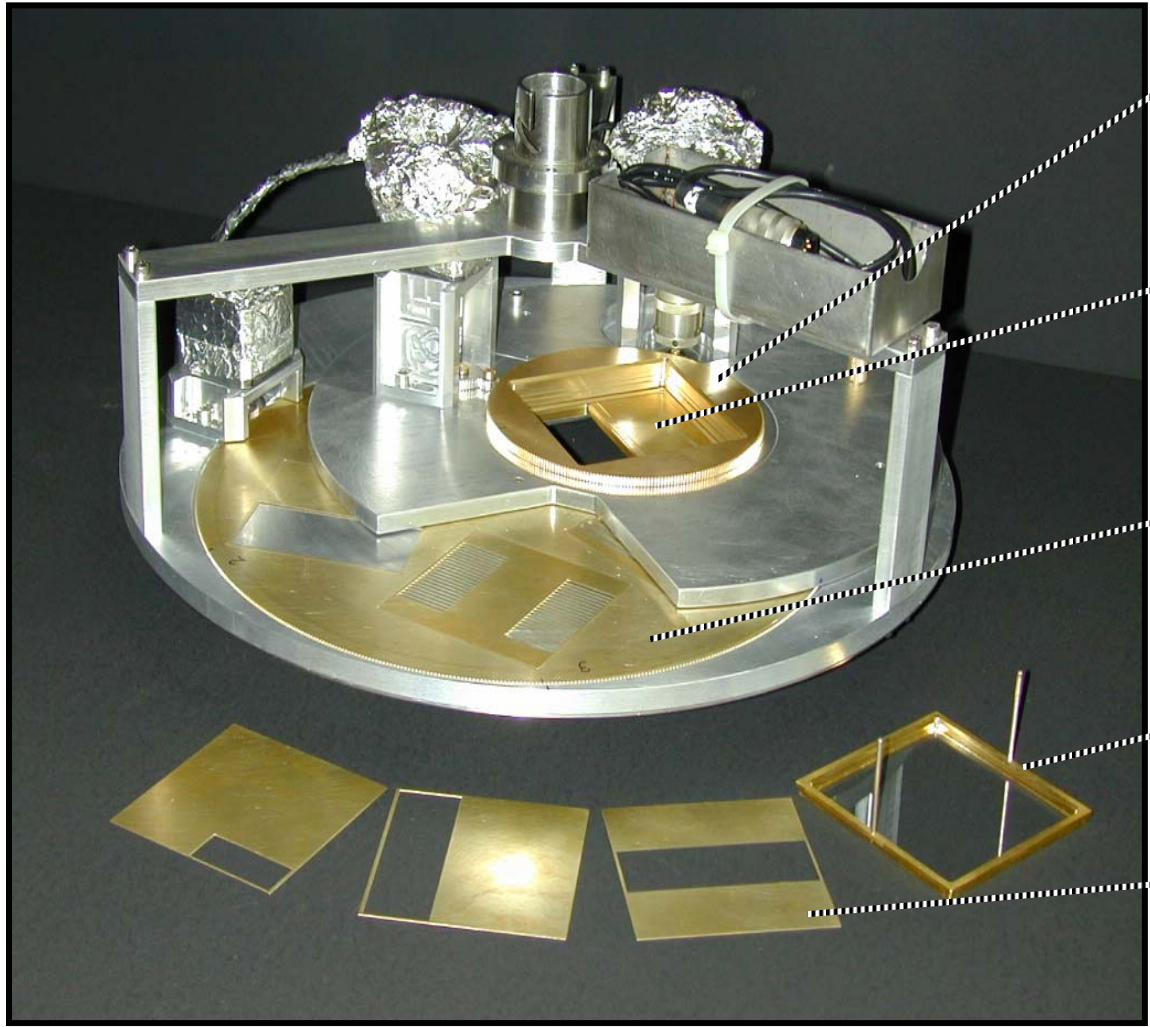


shutter

quartz
source



Instrumentation



**positionable
substrate
holder**

shutter-mask

**positionable
holder for up to
five masks**

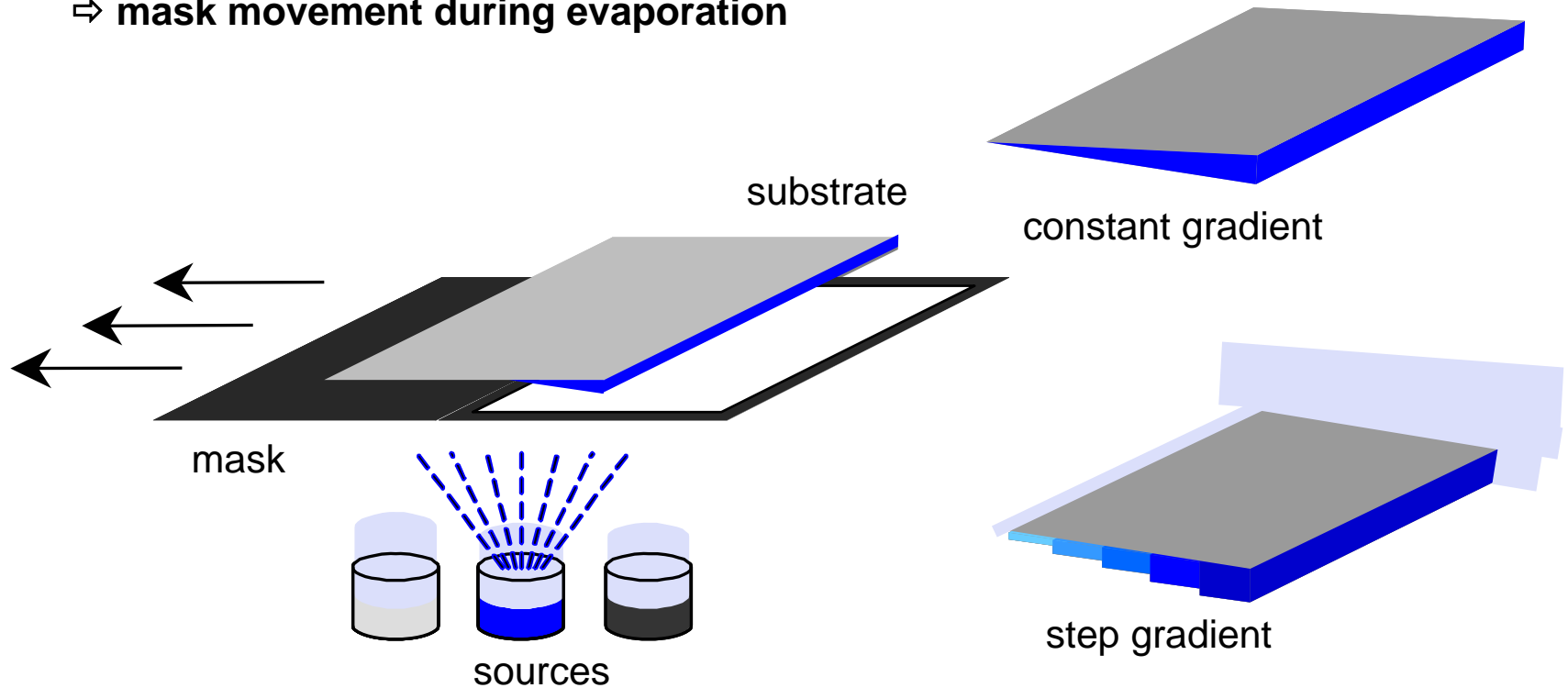
substrate holder

selection of masks

Combinatorial Vapor Deposition

Preparation of thickness gradients

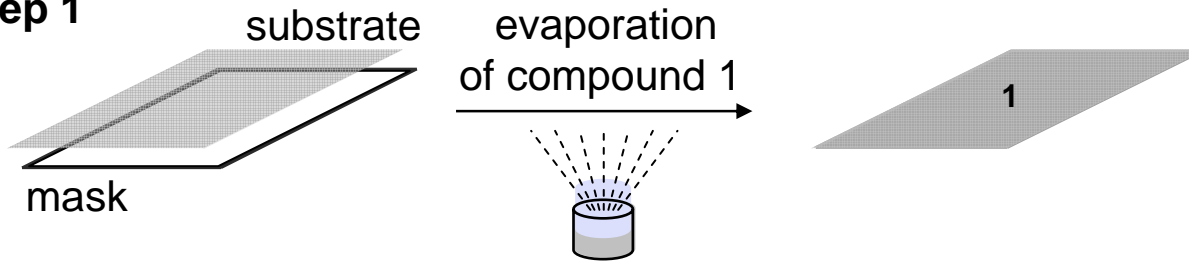
⇒ mask movement during evaporation



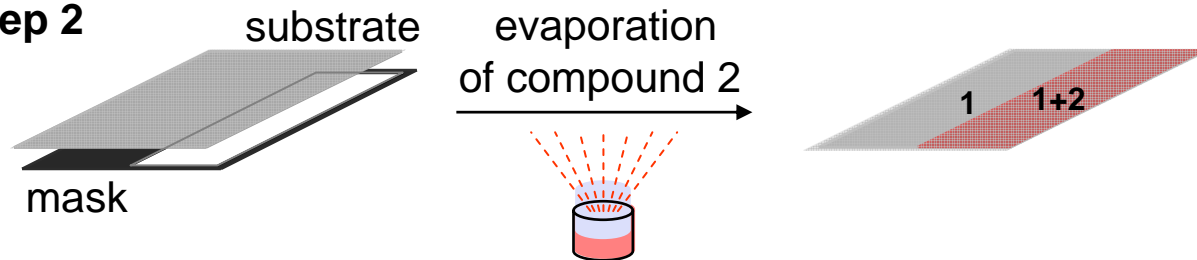
Combinatorial Vapor Deposition

Preparation of sectors

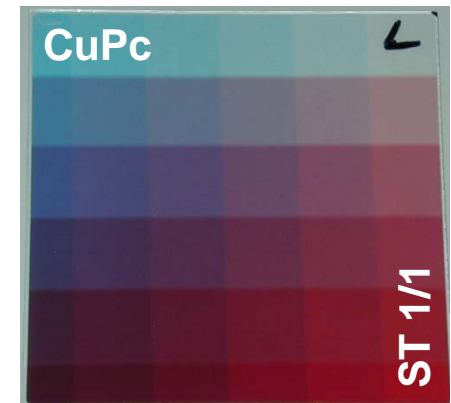
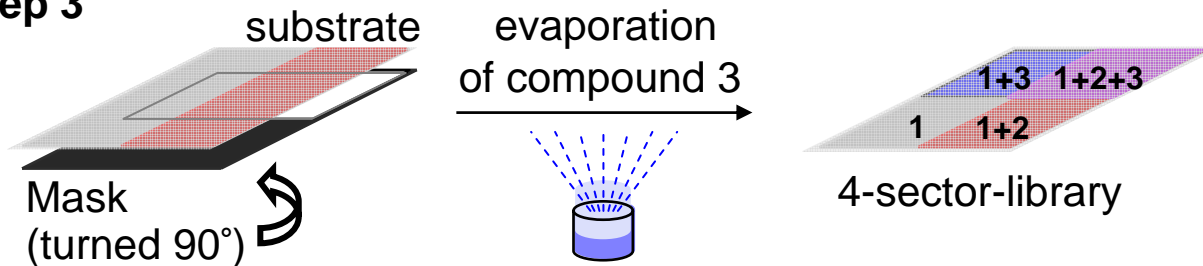
Step 1



Step 2



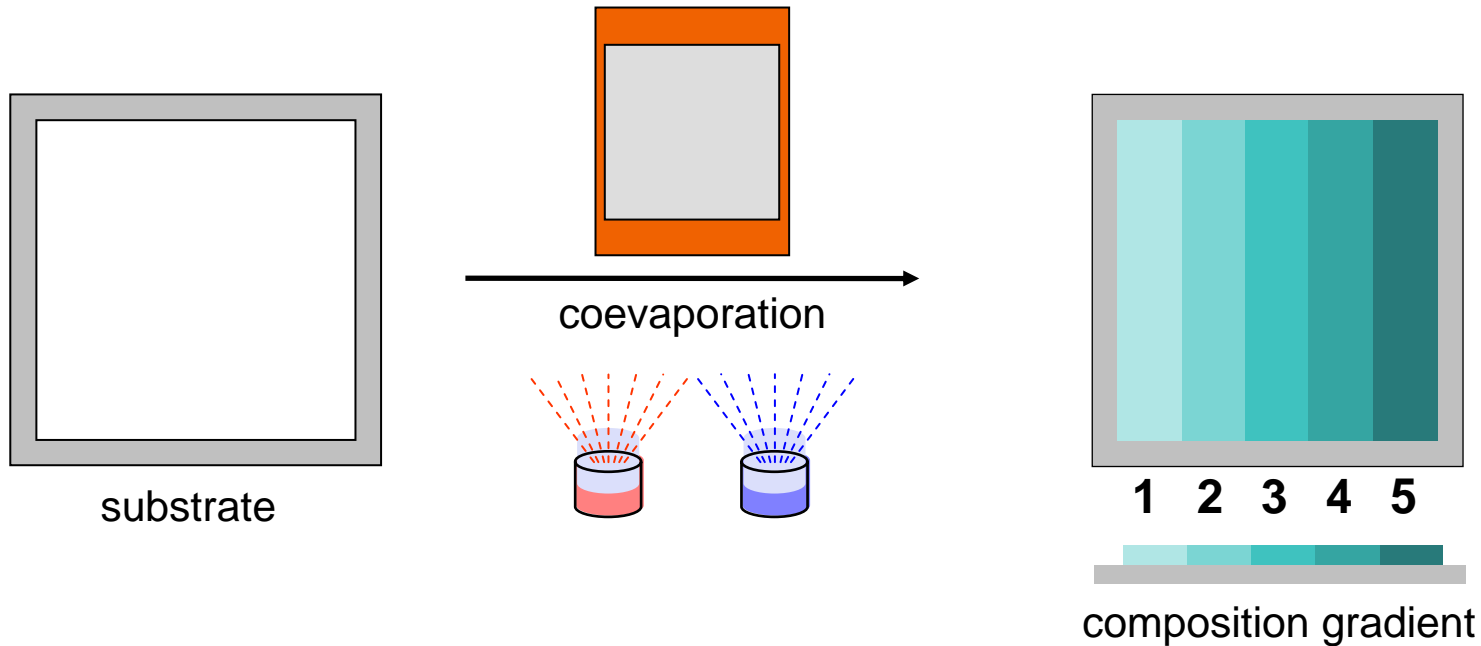
Step 3



Combinatorial Vapor Deposition

Preparation of compositions

⇒ Simultaneous evaporation of two or more compounds with different deposition rates



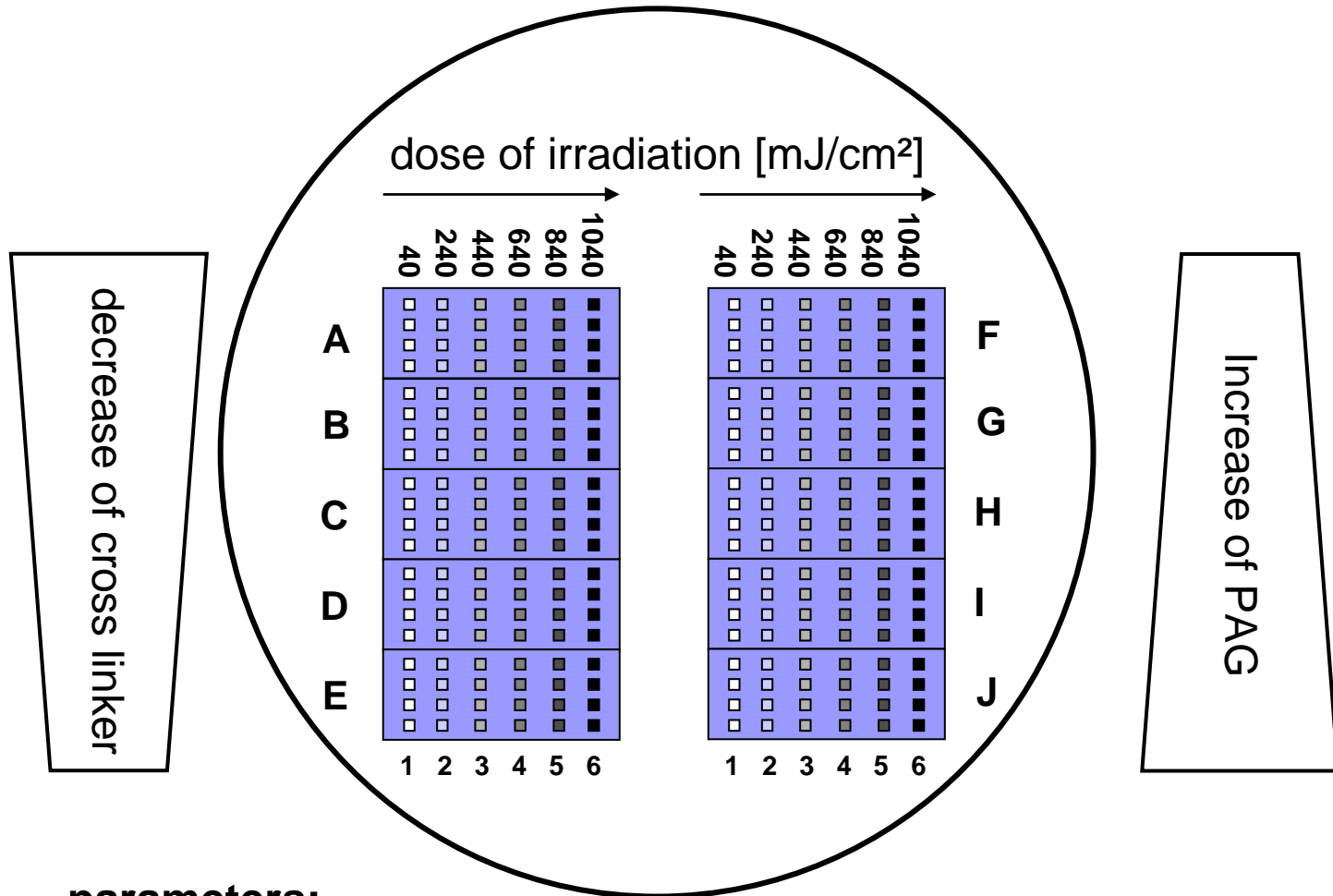


Combinatorial Vapor Deposition

Advantages of a combinatorial approach

- much faster than conventional methods
- defined **layer thickness control** in the nanometer range
- efficient screening of **material combinations**
(completely insoluble materials are applicable, e.g. adamantane derivatives or fluoro compounds for 193 lithography)
- defined preparation of **material composition**
(internal gradients within one layer or well-defined layer sequences)
- simultaneous optimization of parameters in **one experiment under identical conditions**
- in-situ preparation of **reference devices**

Combinatorial Library



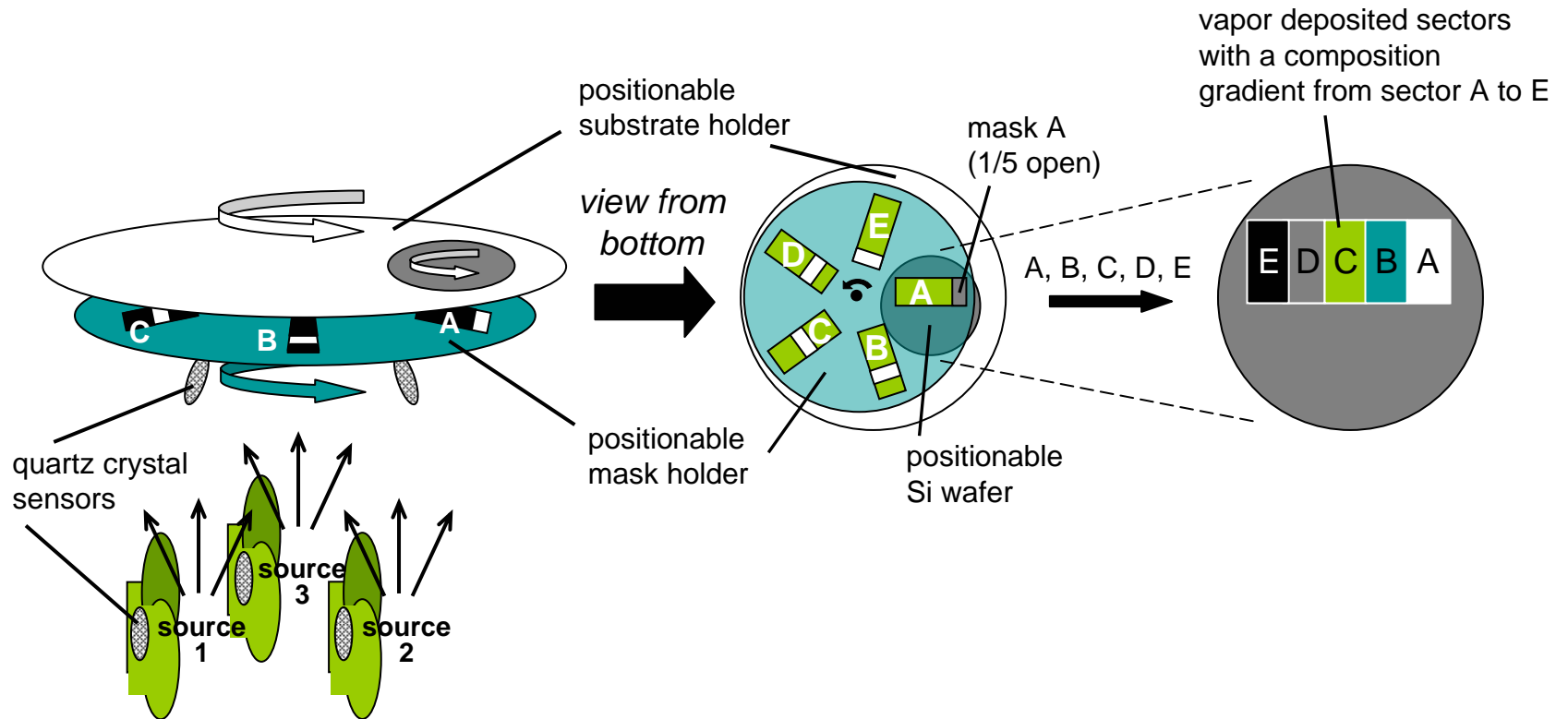
parameters:

exposure dose increases from 40 to 1040 mJ/cm² at 365 nm.

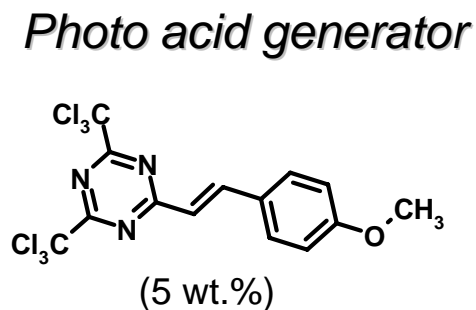
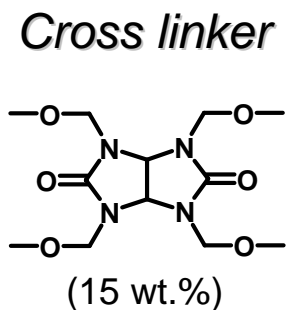
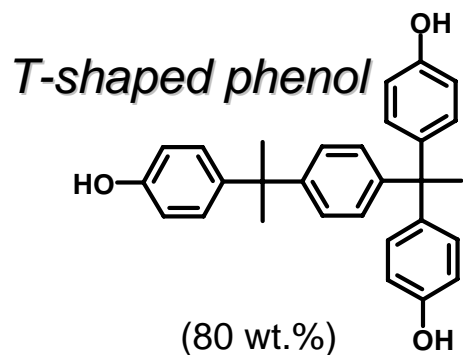
PEB 90 °C for 30 s

Development: varying TMAH concentration and development times

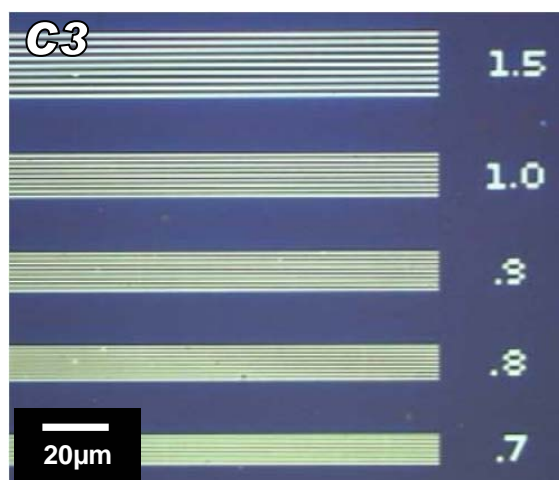
Combinatorial Vapor Deposition of Molecular Glass Photoresists



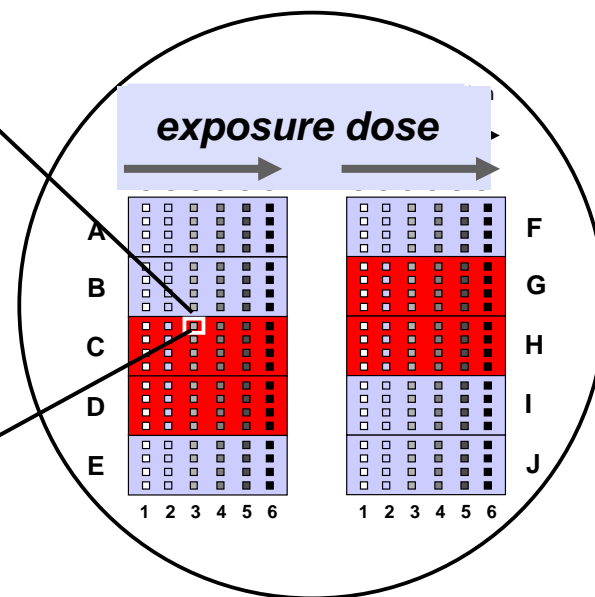
Combinatorial Vapor Deposition of Molecular Glass Photoresists



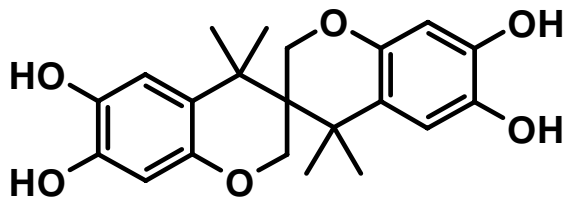
Photopatterning of evaporated libraries



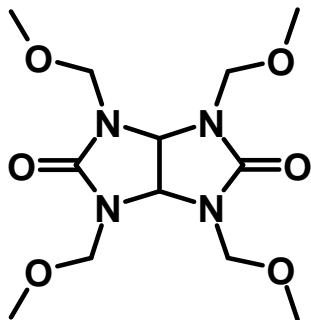
aqueous base development



Environmentally Friendly Molecular Glass Photoresists



Spirobichroman



Cross linker

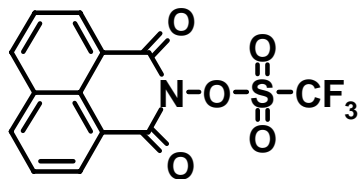


Photo acid generator



**77.6wt.% spirobichroman, 20.2wt.% cross linker,
2.2wt.% triflate**

exposure dose 840 mJ/cm² at 365 nm.

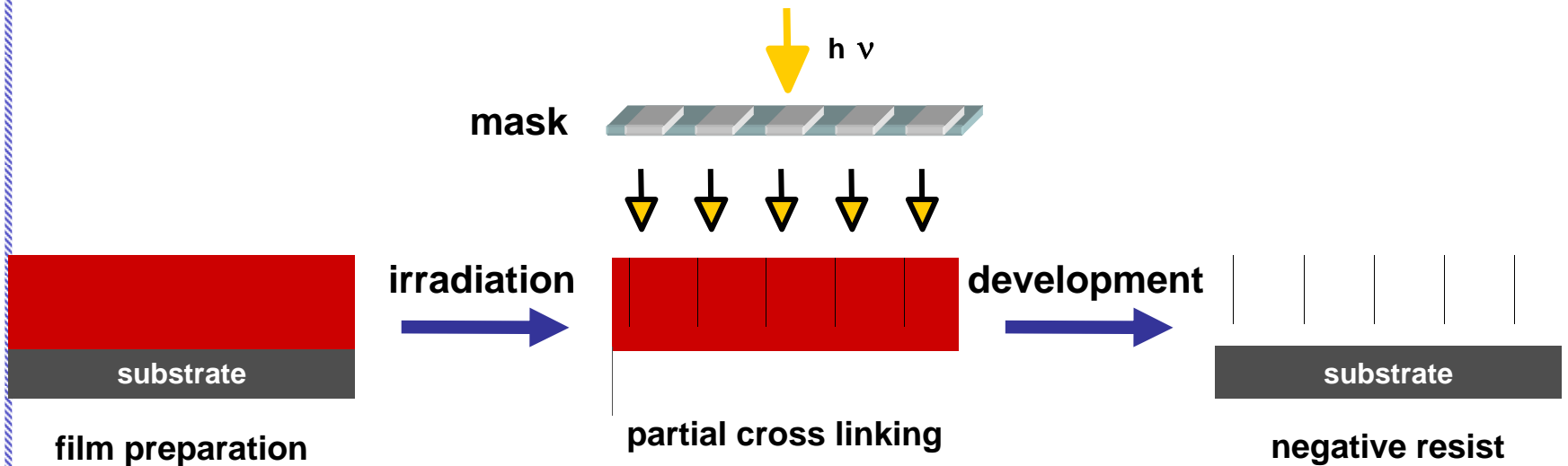
PEB 90 °C for 30 s, development pure deionized water



Outline

- Physical Vapor Deposition (PVD)
 - Process
 - Benefits
 - Materials Requirements
- Novelty of PVD Process
 - Combinatorial Processing
 - Composition Gradients
- **All-Dry Lithography**
 - **Processes**
 - **Results**

On the Way Towards Solvent Free Photopatterning



Film preparation

solution *state of the art*

dry *on going research*

Physical Vapor Deposition

Development

solution *state of the art*

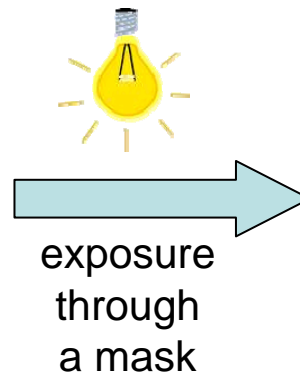
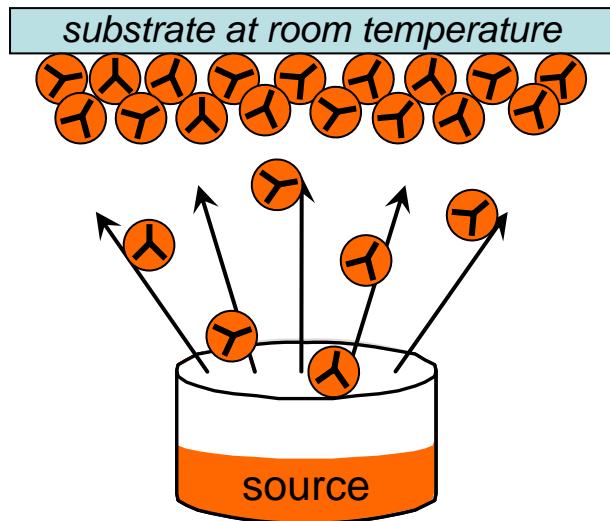
dry *on going research*

Vacuum development

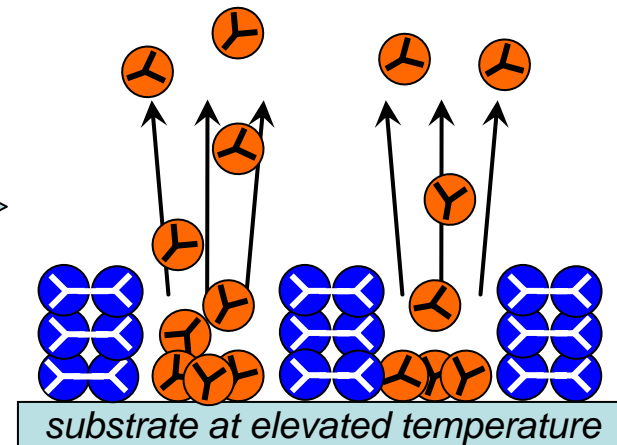
Solvent-Free Photopatterning

Contrast is realized by changing molecular weight or intermolecular interactions

Film preparation by PVD



Vacuum development

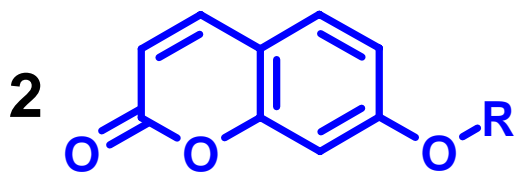


Important advantages:

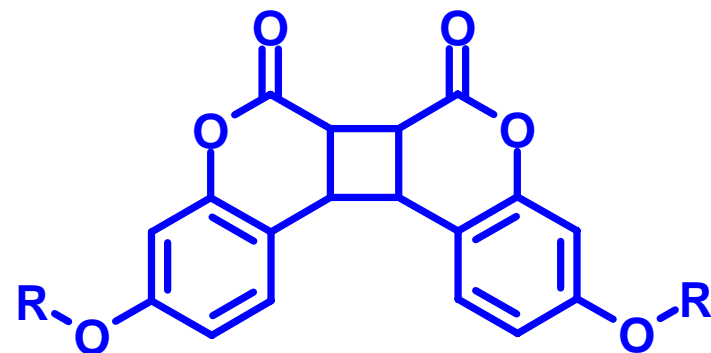
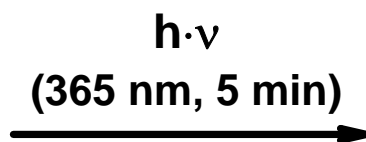
- no PAB and PEB necessary
- no solvent residues (plasticizer)
- no capillary forces

Solvent-Free Photopatterning

[2+2]-Cycloaddition



Coumarine derivative

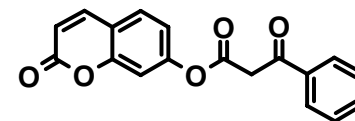
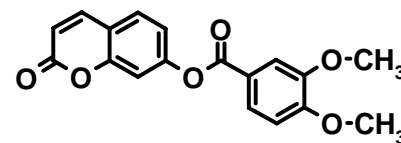
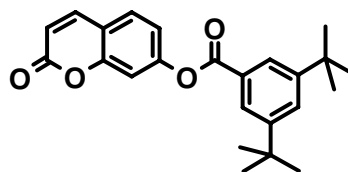
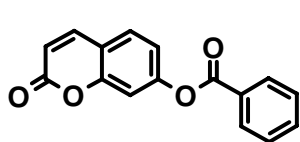


Dimer with an enhanced molecular weight

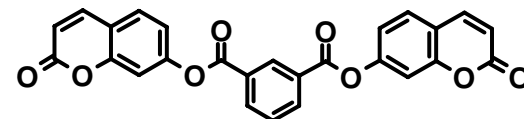
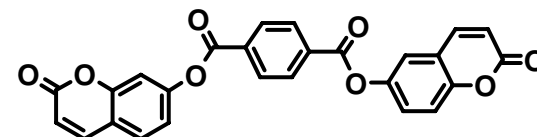
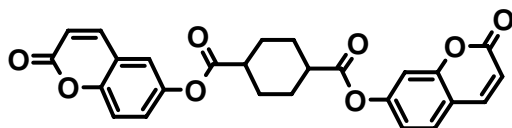
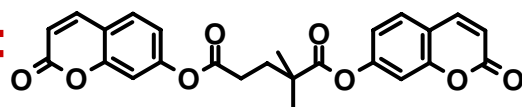
On the Way Towards Solvent-Free Photopatterning

Synthesized coumarine derivatives:

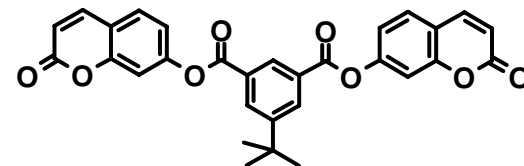
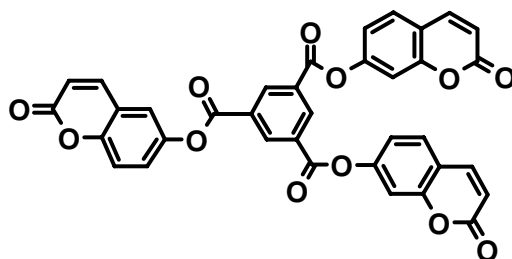
Mono-esters:



Bis-esters:



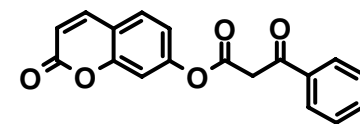
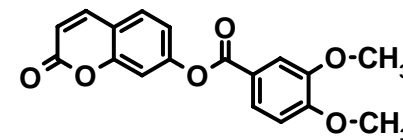
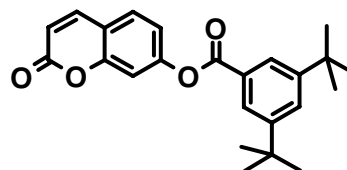
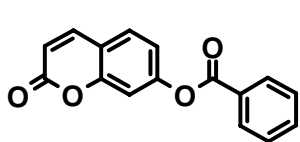
Tris-ester:



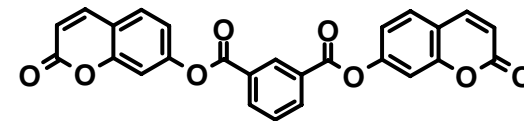
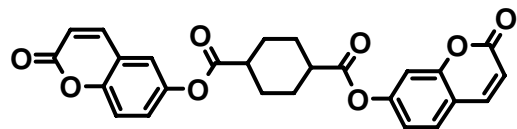
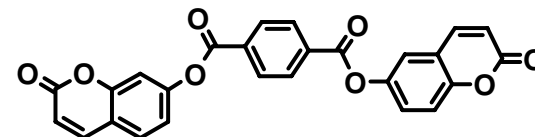
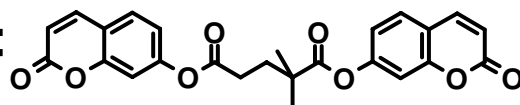
On the Way Towards Solvent-Free Photopatterning

Synthesized coumarine derivatives:

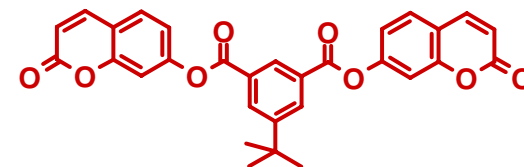
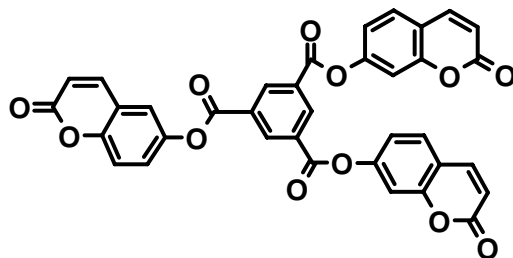
Mono-esters:



Bis-esters:

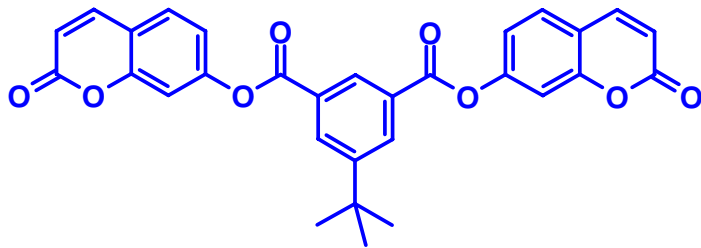


Tris-ester:



amorphous glass,
but not long-term stable

All-Dry Photopatterning



Bis-coumarin ester



Conditions:

Evaporation of bis-coumarine ester

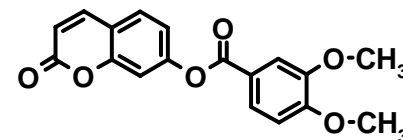
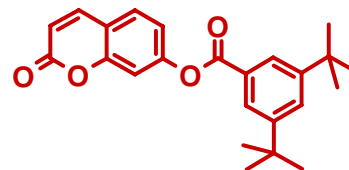
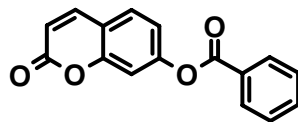
Exposure: 15 min at 365 nm

Vacuum development: 15h, 120°C, 10⁻⁵ mbar

On the Way Towards Solvent-Free Photopatterning

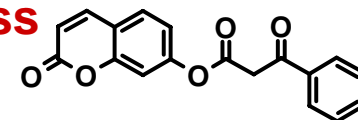
Synthesized coumarine derivatives:

Mono-esters:

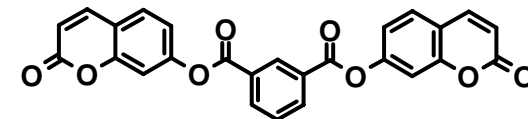
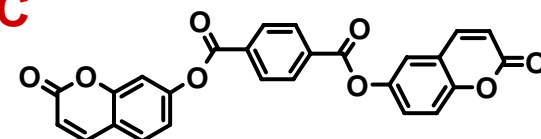
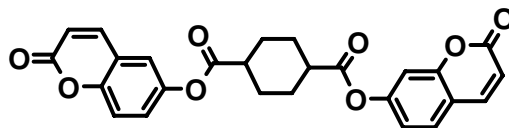
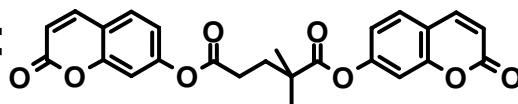


amorphous stable glass

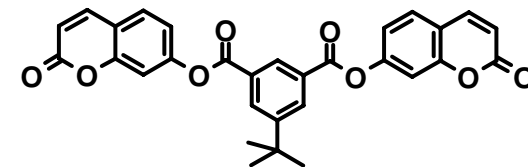
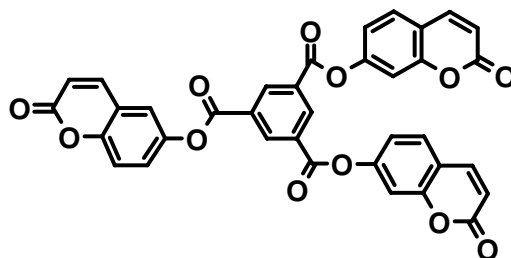
T_g : 33 °C
 T_m : 134 °C
 T_{decomp} : 252 °C



Bis-esters:



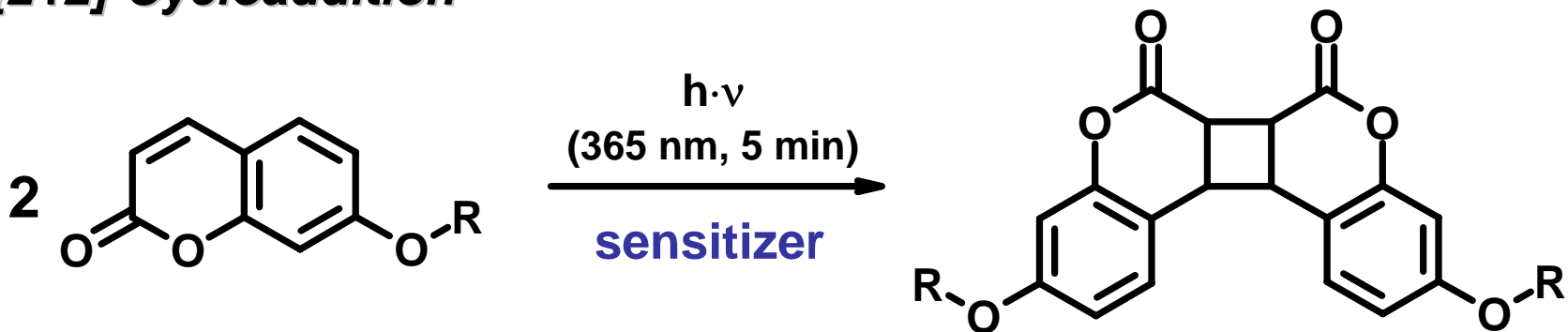
Tris-ester:



Solvent-Free Photopatterning

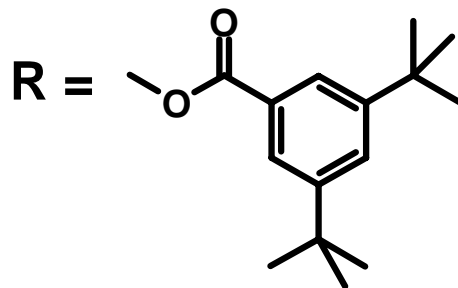
First system realized by utilizing coumarine derivatives

[2+2]-Cycloaddition

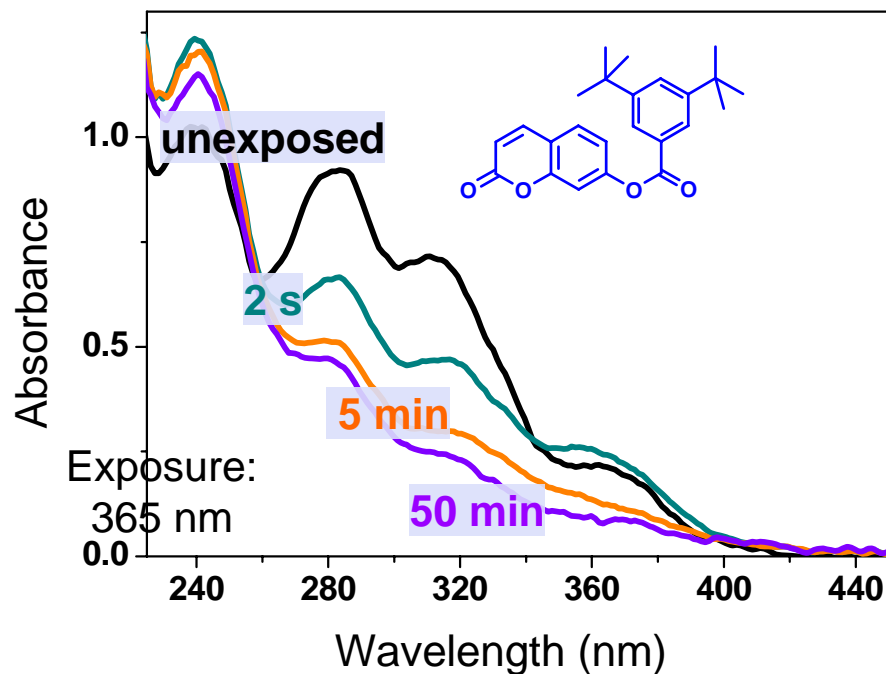


Coumarine derivative

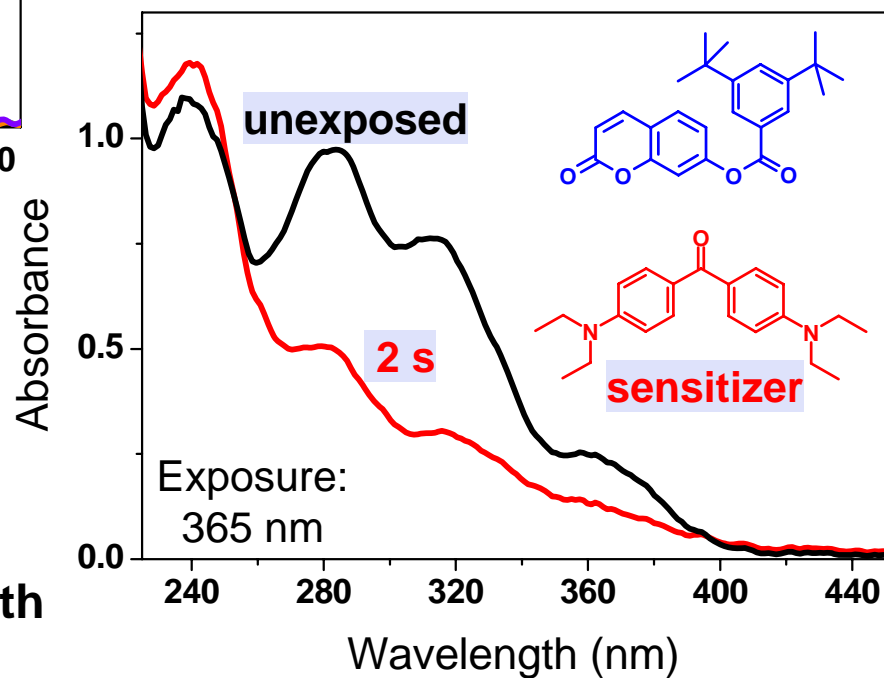
Dimer with increased molecular weight



UV-Vis Characterization of Cycloaddition

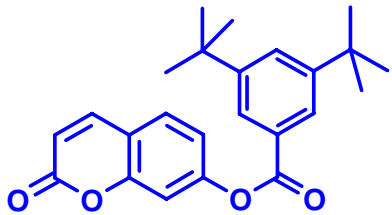


Coevaporation

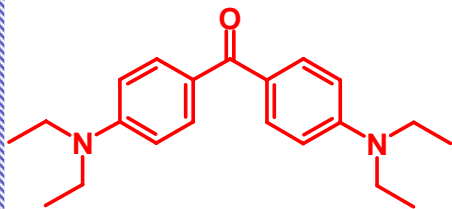


⇒ Clear increase of sensitivity by the coevaporation of the coumarin with the Michlers ethyl keton

All-Dry Photopatterning

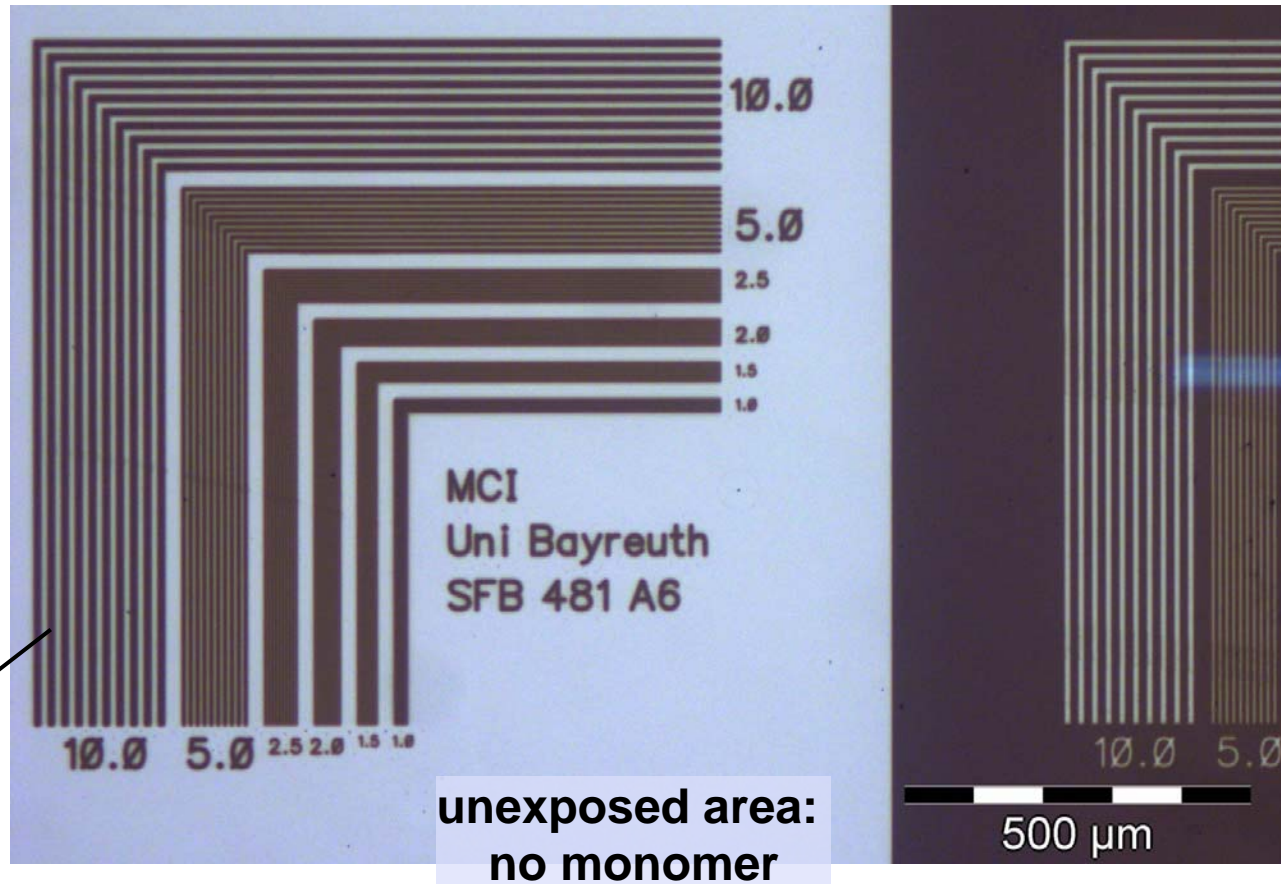


Mono-coumarin ester



sensitizer

exposed area:
dimer



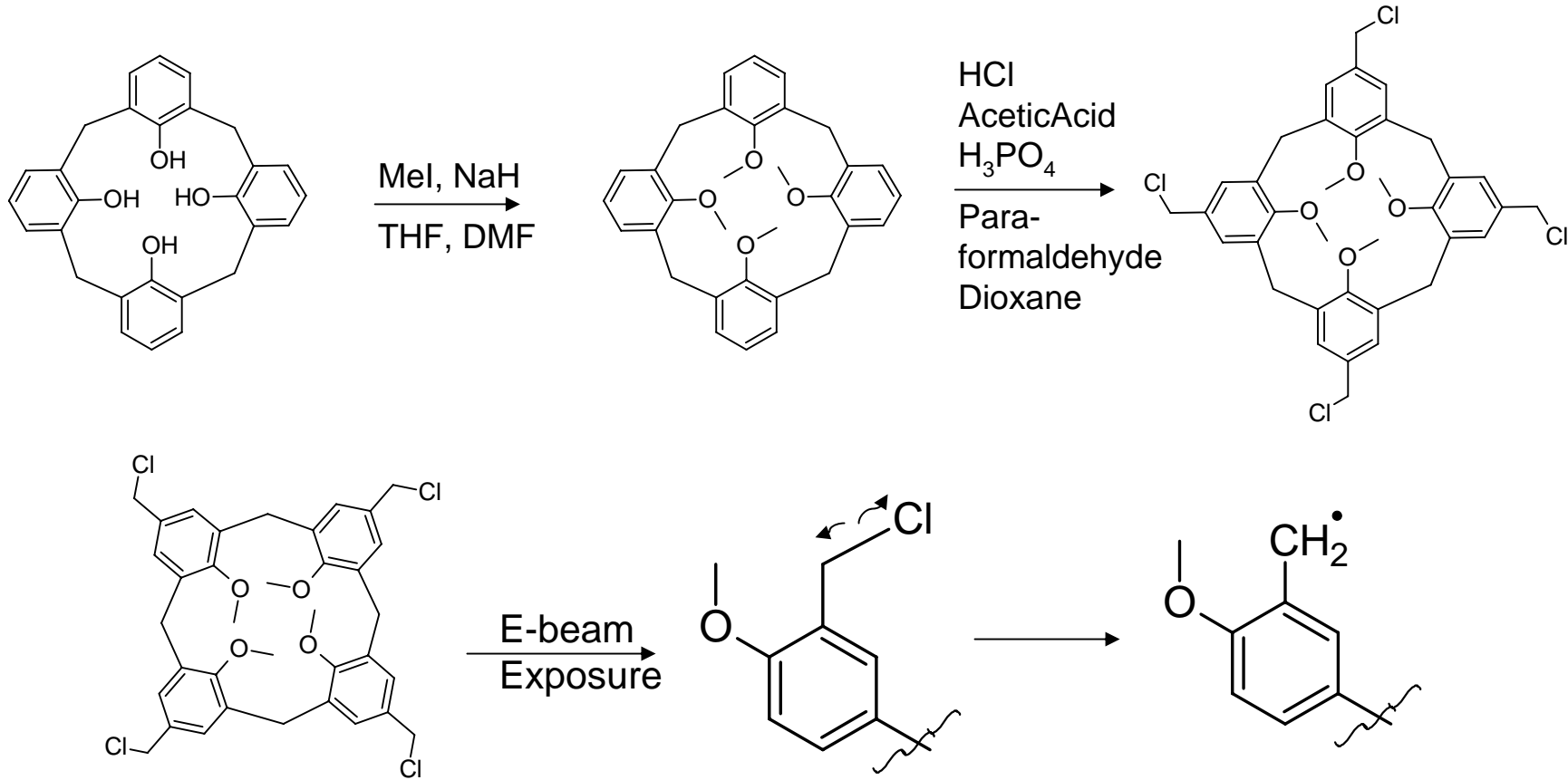
Conditions:

Coevaporation of coumarine ester and sensitizer (10wt%)

Exposure: 5 min at 365 nm

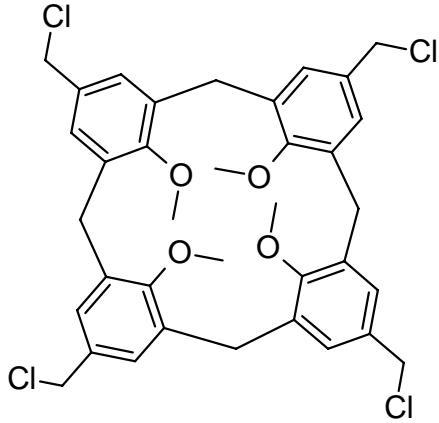
Vacuum development: 15h, 80°C, 10⁻⁵ mbar

All-Dry Photopatterning



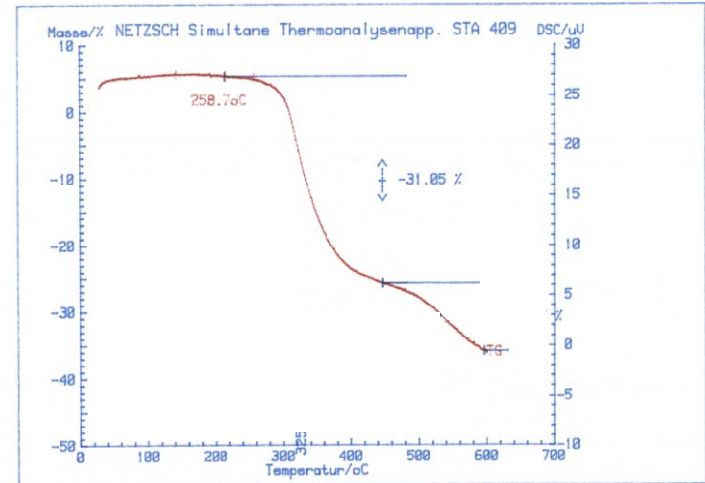
Free radicals generated upon E-beam exposure, radicals will combine to form a dense phenolic network

All-Dry Photopatterning



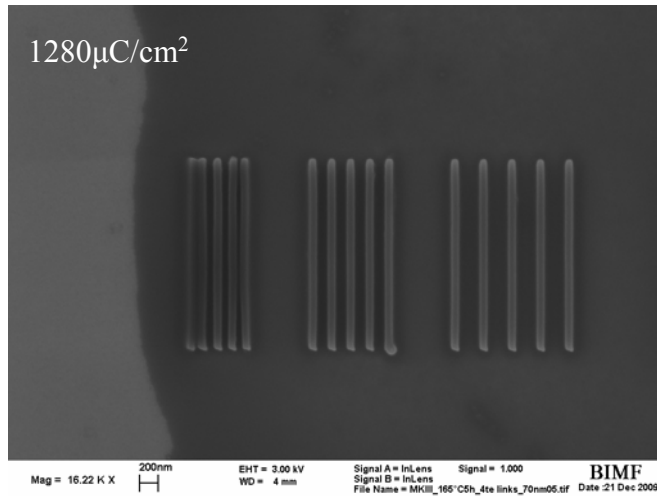
**Successfully vapor deposited
on HMDS primed silicon wafer**

Evaporation temperature: 170°C

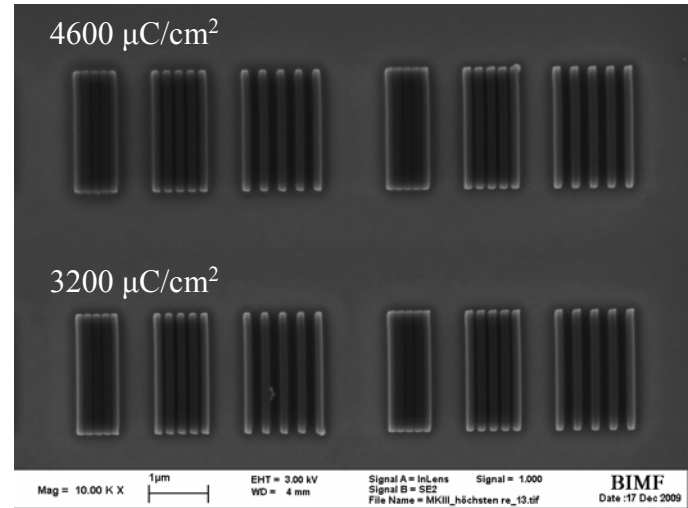


**TGA shows good
thermal stability**

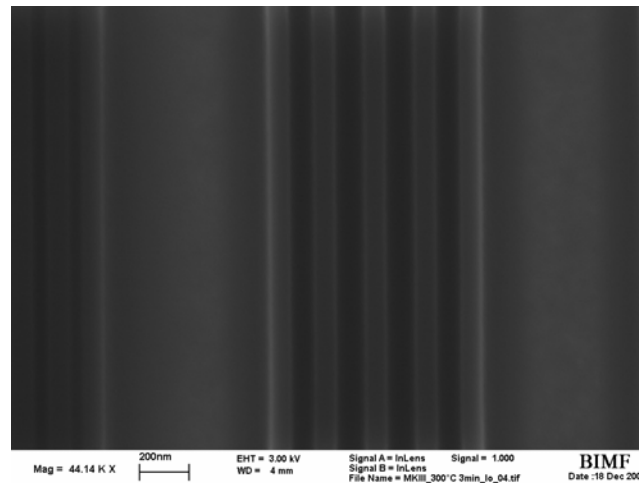
All-Dry Photopatterning



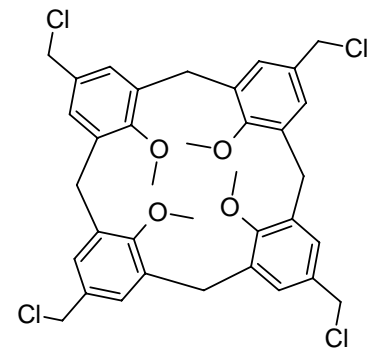
Development: 5h @ 165°C high vacuum



Development: 10min @ 260°C high vacuum



Development: 3 min. @ 300°C high vacuum



Acknowledgements

Cornell University

Prof. Christopher K. Ober

Dr. Jin-Kyun Lee

Ober Group



University of Bayreuth

Prof. Hans-Werner Schmidt

Frauke Pfeiffer

Christian Neuber

Tristan Kolb



Semiconductor Research Corporation (SRC) for funding